



UPDATED 12/07/2007

5.90-7.20 GHz 4-Watt Internally Matched Power FET

FEATURES

- 5.90-7.20GHz Bandwidth
- Input/Output Impedance Matched to 50 Ohms
- +36.5 dBm Output Power at 1dB Compression
- 9.0 dB Power Gain at 1dB Compression
- 32% Power Added Efficiency
- -46 dBc IM3 at PO = 29.5 dBm SCL
- **Hermetic Metal Flange Package**
- 100% Tested for DC, RF, and R_{TH}





Caution! ESD sensitive device. **ELECTRICAL CHARACTERISTICS (Ta = 25°C)**

SYMBOL	PARAMETERS/TEST CONDITIONS ¹	MIN	TYP	MAX	UNITS
P _{1dB}	Output Power at 1dB Compression $f = 5.90-7.20GHz$ $V_{DS} = 10 \text{ V}, I_{DSQ} \approx 1100\text{mA}$	35.5	36.5		dBm
G _{1dB}	Gain at 1dB Compression $f = 5.90-7.20GHz$ $V_{DS} = 10 \text{ V}, I_{DSQ} \approx 1100\text{mA}$	8.0	9.0		dB
ΔG	Gain Flatness $f = 5.90-7.20GHz$ $V_{DS} = 10 \text{ V}, I_{DSQ} \approx 1100\text{mA}$			±0.8	dB
PAE	Power Added Efficiency at 1dB Compression V_{DS} = 10 V, $I_{DSQ} \approx 1100$ mA f = 5.90-7.20GHz		32		%
Id _{1dB}	Drain Current at 1dB Compression f = 5.90-7.20GHz		1200	1400	mA
IM3	Output 3rd Order Intermodulation Distortion Δf = 10 MHz 2-Tone Test; Pout = 29.5 dBm S.C.L ² V_{DS} = 10 V, I_{DSQ} ≈ 65% IDSS f = 7.20GHz	-43	-46		dBc
I _{DSS}	Saturated Drain Current $V_{DS} = 3 V$, $V_{GS} = 0 V$		2000	2500	mA
V_P	Pinch-off Voltage $V_{DS} = 3 \text{ V}, I_{DS} = 20 \text{ mA}$		-2.5	-4.0	V
R _{TH}	Thermal Resistance ³		5.5	6.0	°C/W

Note: 1) Tested with 100 Ohm gate resistor.

ABSOLUTE MAXIMUM RATING^{1,2}

SYMBOLS	PARAMETERS	ABSOLUTE ¹	CONTINUOUS ²	
V _{DS}	Drain-Source Voltage	15	10V	
V_{GS}	Gate-Source Voltage	-5	-4V	
lgsf	Forward Gate Current	43.2mA	14.4mA	
lgsr	Reverse Gate Current	-7.2mA	-2.4mA	
Pin	Input Power	35.5dBm	@ 3dB Compression	
Tch	Channel Temperature	175 °C	175 °C	
Tstg	Storage Temperature	-65 to +175 °C	-65 to +175 °C	
Pt	Total Power Dissipation	25W	25W	

1. Exceeding any of the above ratings may result in permanent damage.

²⁾ S.C.L. = Single Carrier Level.

³⁾ Overall Rth depends on case mounting.

^{2.} Exceeding any of the above ratings may reduce MTTF below design goals.





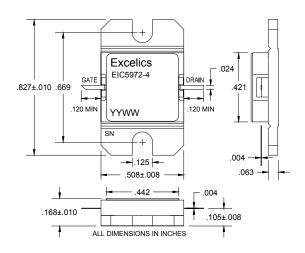
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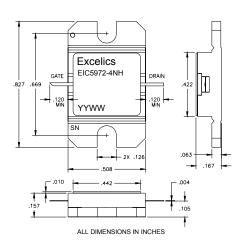
PACKAGES OUTLINE

Dimensions in inches, Tolerance + .005 unless otherwise specified

EIC5972-4 (Hermetic)









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ORDERING INFORMATION

Part Number	Packages	Grade ¹	f _{Test} (GHz)	P _{1dB} (min)	IM ₃ (min) ²
EIC5972-4	Hermetic	Industrial	5.90-7.20GHz	35.5	-43
EIC5972-4NH	Non-Hermetic	Industrial	5.90-7.20GHz	35.5	-43

Notes:

- 1. Contact factory for military and hi-rel grades.
- 2. Exact test conditions are specified in "Electrical Characteristics" table.

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